1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in Trench MOSFET technology and NPN Resistor-Equipped Transistor (RET) together in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Trench MOSFET technology
- NPN transistor built-in bias resistors
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction

3. Applications

- Charging switch for portable devices
- High-side load switch
- USB port overvoltage protection
- Power management in battery-driven portables
- Hard disk and computing power management

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P-channel Tre	nch MOSFET						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-3.4	Α
P-channel Tre	nch MOSFET; static ch	aracteristics					,
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.6 A; T_j = 25 °C		-	85	110	mΩ
NPN RET			'	'	·		
V_{CEO}	collector-emitter voltage	T _{amb} = 25 °C; open base		-	-	50	V
I _O	output current			-	-	100	mA



30 V P-channel MOSFET with pre-biased NPN transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NPN RET						,
R1	bias resistor 1		3.3	4.7	6.1	kΩ
R2	bias resistor 2		-	47	-	kΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm²

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	6 5 4	C G S
2	В	base		
3	D	drain	7 8	
4	S	source		R_2
5	G	gate	1 2 3	
6	С	collector	Transparent top view DFN2020-6 (SOT1118)	E B D 017aaa396
7	С	collector	DI 142020-0 (0011110)	017.aaa390
8	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PMC85XP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMC85XP	1K

PMC85XP

30 V P-channel MOSFET with pre-biased NPN transistor

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
P-channel	Trench MOSFET					
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-3.4	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.6	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	485	mW
			[1]	-	1170	mW
		$T_{sp} = 25 ^{\circ}C$	[2]	-	8300	mW
P-channel	Trench MOSFET; source-drain	diode				
Is	source current	T _{amb} = 25 °C	[1]	-	-1.2	Α
NPN RET	·					-
V_{CBO}	collector-base voltage	T _{amb} = 25 °C; open emitter		-	50	V
V_{CEO}	collector-emitter voltage	T _{amb} = 25 °C; open base		-	50	V
V _{EBO}	emitter-base voltage	T _{amb} = 25 °C; open collector		-	10	V
VI	input voltage	positive		-	30	V
		negative		-	-5	V
I_{O}	output current			-	100	mA
I_{CM}	peak collector current			-	100	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	465	mW
			[1]	-	985	mW
		T _{sp} = 25 °C	[2]	-	4160	mW
Per device)					
T_j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm²

PMC85XP

All information provided in this document is subject to legal disclaimers.

^[2] Device mounted on an FR4 PCB, single-sided copper; tin-plated and standard footprint.

30 V P-channel MOSFET with pre-biased NPN transistor

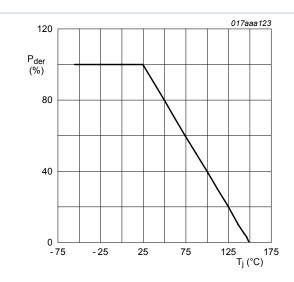


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

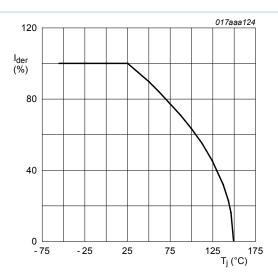
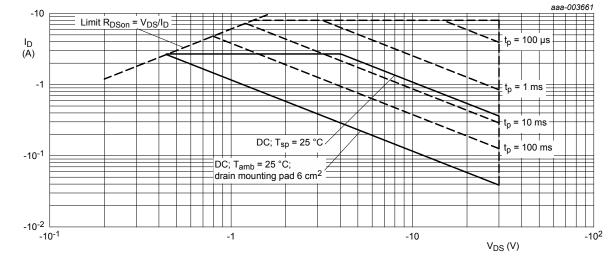


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
P-channel	P-channel Trench MOSFET							
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	223	256	K/W	
		[2]	-	93	107	K/W		
	ambient	t ≤ 5 s; in free air	[2]	-	55	63	K/W	
PMC85XP	1	All information provided in this document is subject to le	egal disclaimers.		© Nexper	ia B.V. 2017. A	All rights reserv	

Product data sheet 15 May 2013 4 / 15

30 V P-channel MOSFET with pre-biased NPN transistor

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W
NPN RET			,				
R _{th(j-a)}	thermal resistance	in free air	[1]	-	233	270	K/W
from junction to ambient			[2]	-	110	127	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm²

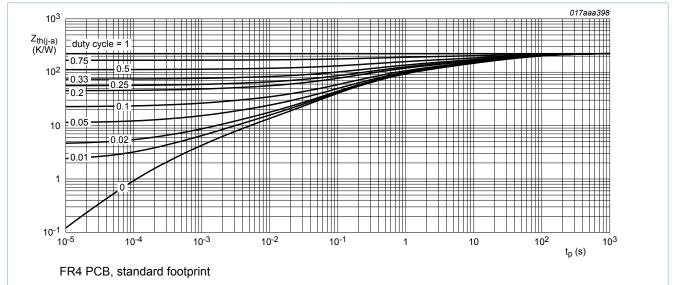


Fig. 4. P-channel Trench MOSFET: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V P-channel MOSFET with pre-biased NPN transistor

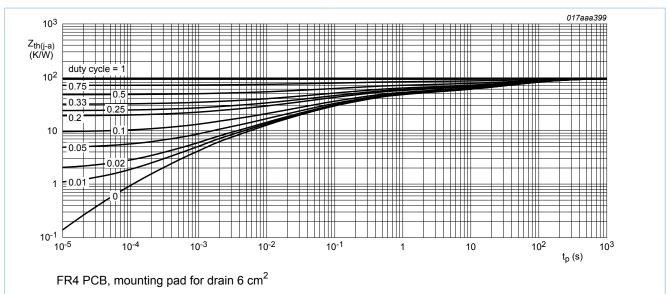


Fig. 5. P-channel Trench MOSFET: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P-channel	Trench MOSFET; static cha	aracteristics				
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 mA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.78	-1	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _{amb} = 25 °C	-	-	-1	μA
		V _{DS} = -30 V; V _{GS} = 0 V; T _{amb} = 150 °C	-	-	-11	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -2.6 A; T_j = 25 °C	-	85	110	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -2.6 A; T_j = 150 °C	-	133	173	mΩ
		V_{GS} = -2.5 V; I_D = -1.5 A; T_j = 25 °C	-	105	140	mΩ
g _{fs}	transfer conductance	V_{DS} = -10 V; I_{D} = -2.6 A; T_{j} = 25 °C	-	10	-	S
P-channel	Trench MOSFET; dynamic	characteristics				
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -2.6 A; V_{GS} = -4.5 V;	-	5.2	7.8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.1	-	nC
Q_{GD}	gate-drain charge		-	0.95	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	680	-	pF
C _{oss}	output capacitance	output capacitance $T_j = 25 ^{\circ}\text{C}$		54	-	pF
MC85XP		All information provided in this document is subject to legal disclaimers.		© Nexper	ia B.V. 2017.	All rights rese

30 V P-channel MOSFET with pre-biased NPN transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rss}	reverse transfer capacitance		-	40	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I_{D} = -2.6 A; $R_{G(ext)}$ = 6 Ω ;	-	3	-	ns
t _r	rise time	$V_{GS} = -4.5 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	15	-	ns
$t_{d(off)}$	turn-off delay time		-	112	-	ns
t _f	fall time		-	48	-	ns
P-channel	Trench MOSFET; source-dr	ain diode				
V _{SD}	source-drain voltage	I_S = -1.2 A; V_{GS} = 0 V; T_j = 25 °C	-	-0.8	-1.2	V
NPN RET						
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 25 \text{ °C}$	-	-	1	μA
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{j} = 25 \text{ °C}$	-	-	170	μA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 10 mA; T_{j} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_j = 25 \text{ °C}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	I _C = 100 μA; V _{CE} = 5 V; T _j = 25 °C	-	0.6	0.5	V
V _{I(on)}	on-state input voltage	$I_C = 5 \text{ mA}; V_{CE} = 0.3 \text{ V}; T_j = 25 ^{\circ}\text{C}$	1.3	0.9	-	V
R1	bias resistor 1		3.3	4.7	6.1	kΩ
R2	bias resistor 2		-	47	-	kΩ
R2/R1	bias resistor ratio		8	10	12	
C _C	collector capacitance	$I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$ $V_{CB} = 10 \text{ V}$	-	-	2.5	pF

30 V P-channel MOSFET with pre-biased NPN transistor

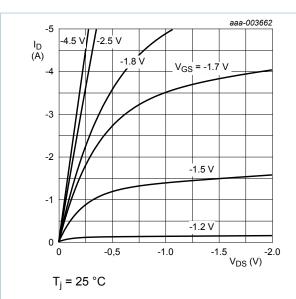
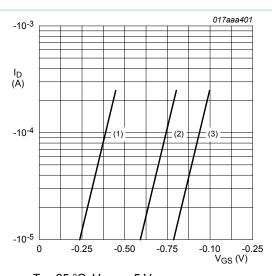


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -5 \,^{\circ}\text{V}$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Subthreshold drain current as a function of gate-source voltage

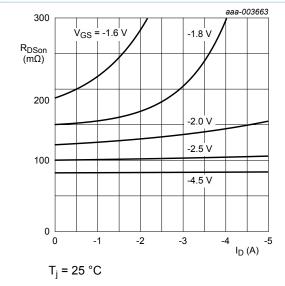


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

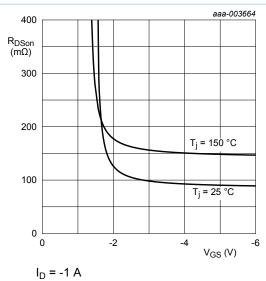
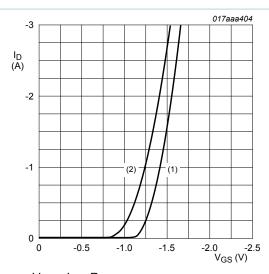


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V P-channel MOSFET with pre-biased NPN transistor



$$V_{DS} > I_{D} \times R_{DSon}$$

(1)
$$T_j = 25 \, ^{\circ}C$$

(2)
$$T_j = 150 \, ^{\circ}C$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

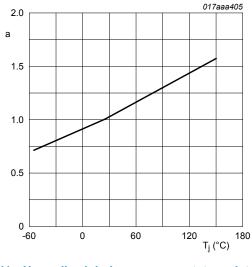
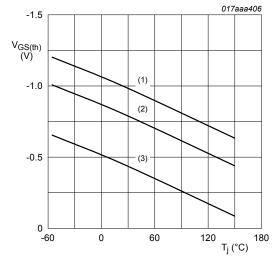


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

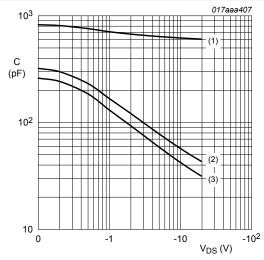
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

PMC85XP

30 V P-channel MOSFET with pre-biased NPN transistor

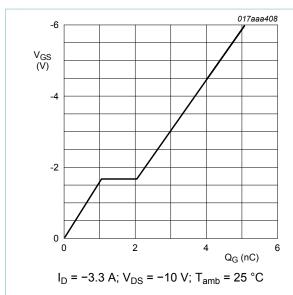


Fig. 14. Gate-source voltage as a function of gate charge; typical values

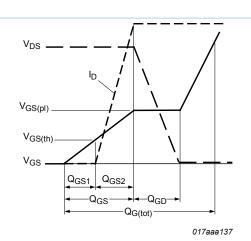
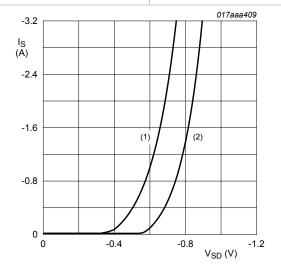


Fig. 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

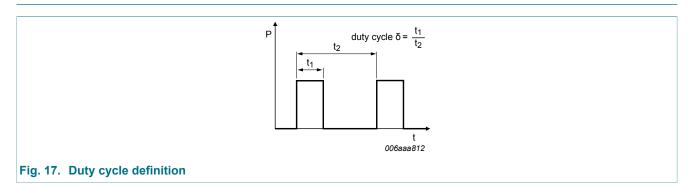
(1) T_{amb} = 150 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

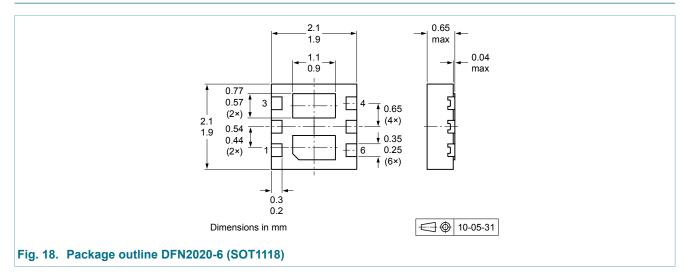
Fig. 16. Source current as a function of source-drain voltage; typical values

30 V P-channel MOSFET with pre-biased NPN transistor

11. Test information

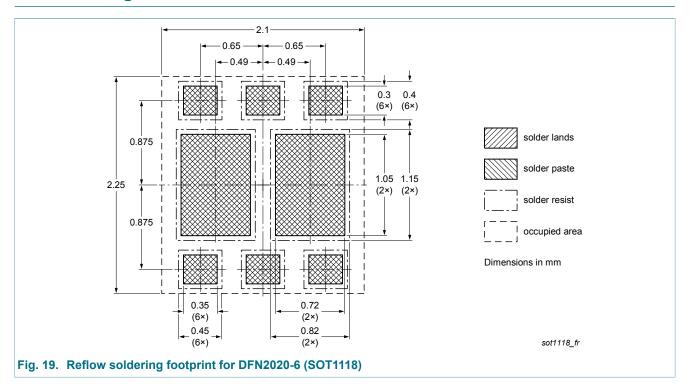


12. Package outline



30 V P-channel MOSFET with pre-biased NPN transistor

13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMC85XP v.2	20130515	Product data sheet	-	PMC85XP v.1		
Modifications:	Pinning information: graphic symbol corrected					
PMC85XP v.1	20120524	Product data sheet	-	-		

30 V P-channel MOSFET with pre-biased NPN transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

15.2 Definitions

Preview — The document is a preview version only. The document is still subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Nexperia takes no responsibility for the content in this document if provided by an information source outside of Nexperia.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia and its suppliers accept no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the

PMC85XP

All information provided in this document is subject to legal disclaimers.

© Nexperia B.V. 2017. All rights reserved

30 V P-channel MOSFET with pre-biased NPN transistor

grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific Nexperia product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Nexperia accepts no liability for inclusion and/or use of nonautomotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

30 V P-channel MOSFET with pre-biased NPN transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	11
12	Package outline	11
13	Soldering	12
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 15 May 2013

[©] Nexperia B.V. 2017. All rights reserved



Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«**FORSTAR**» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: ocean@oceanchips.ru

Web: http://oceanchips.ru/

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А